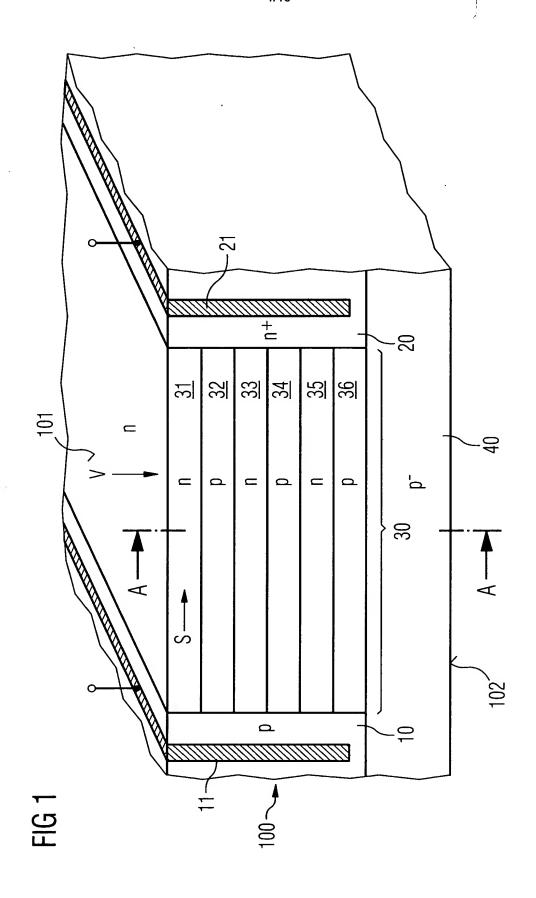
Docket No. IFT975US/I434.103.101 SEMICONDUCTOR COMPONENT WITH INCREASED DIELECTRIC STRENGTH AND/OR REDUCED ON RESISTANCE Gerald Deboy 1/10



Docket No. IFT975US/I434.103.101 SEMICONDUCTOR COMPONENT WITH INCREASED DIELECTRIC STRENGTH AND/OR REDUCED ON RESISTANCE Gerald Deboy 2/10

FIG 2 A-A

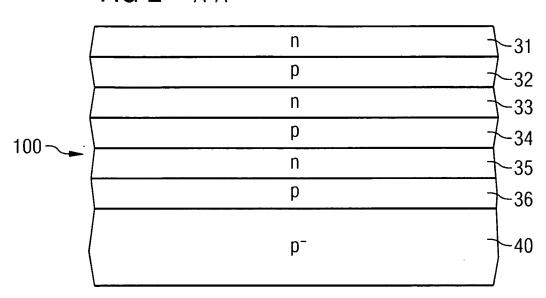
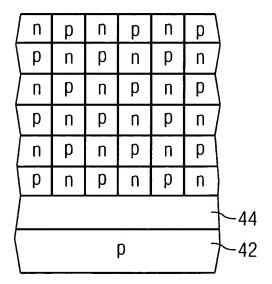


FIG 3



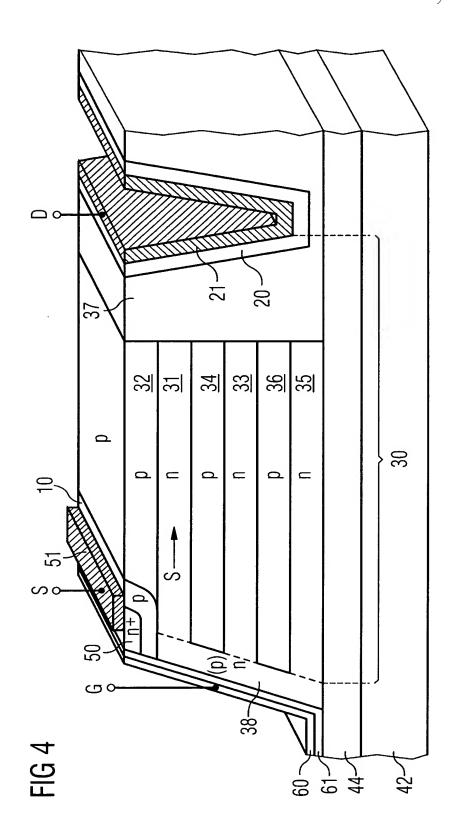
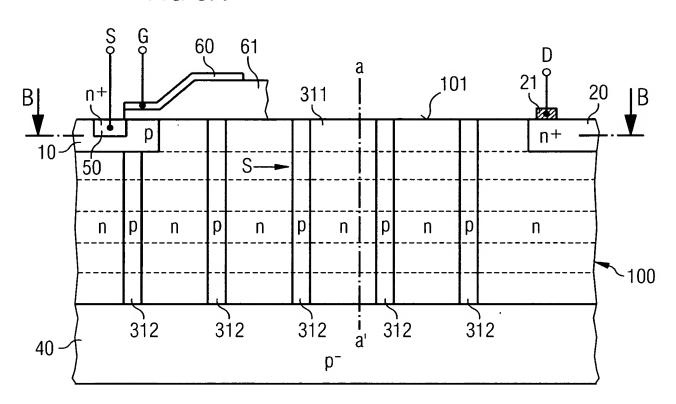
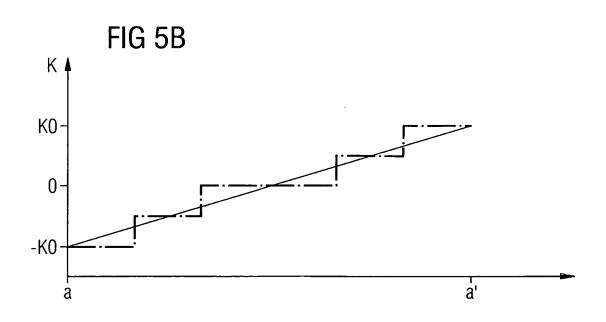


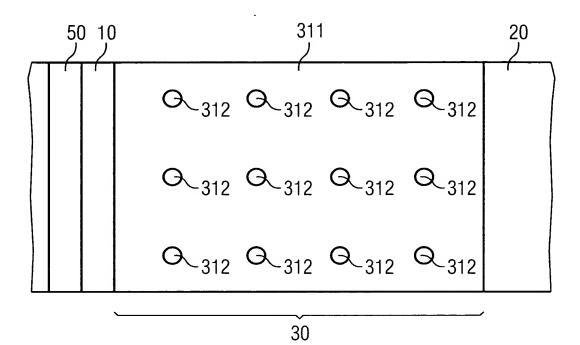
FIG 5A



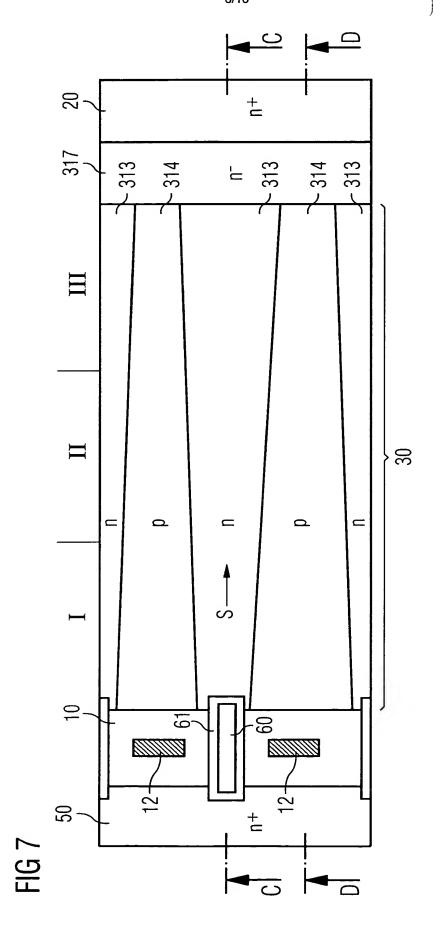


Docket No. IFT975US/I434.103.101 SEMICONDUCTOR COMPONENT WITH INCREASED DIELECTRIC STRENGTH AND/OR REDUCED ON RESISTANCE Gerald Deboy 5/10

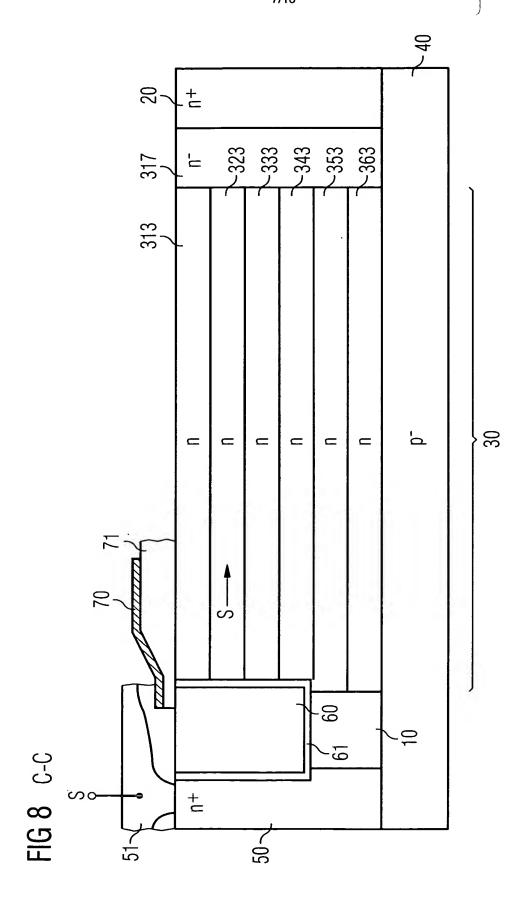
FIG 6 B-B



Docket No. IFT975US/I434.103.101 SEMICONDUCTOR COMPONENT WITH INCREASED DIELECTRIC STRENGTH AND/OR REDUCED ON RESISTANCE Gerald Deboy 6/10



Docket No. IFT975US/I434.103.101 SEMICONDUCTOR COMPONENT WITH INCREASED DIELECTRIC STRENGTH AND/OR REDUCED ON RESISTANCE Gerald Deboy 7/10



Docket No. IFT975US/I434.103.101 SEMICONDUCTOR COMPONENT WITH INCREASED DIELECTRIC STRENGTH AND/OR REDUCED ON RESISTANCE Gerald Deboy 8/10

